# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



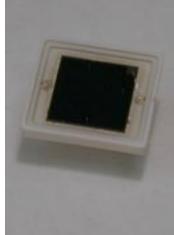
### Contact us

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### PHOTONIC DETECTORS INC.

#### Silicon Photodiode, U.V. Enhanced Photovoltaic Type PDU-V110



**FEATURES** 

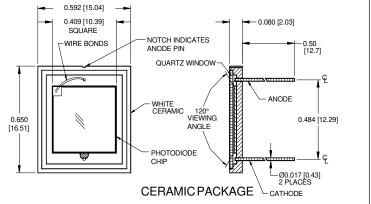
Low noise

U.V.enhanced

Quartz windows

High shunt resistance

#### PACKAGE DIMINSIONS INCH (mm) 0.592 [15.04]



ACTIVE AREA = 100.00 mm<sup>2</sup>

diffused, U.V. enhanced photodiode. Ideal

Packaged in low profile ceramic substrate

The PDU-V110 is a silicon, PIN planar

for low noise photovoltaic applications.

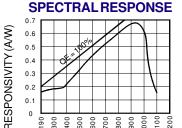
#### **APPLICATIONS**

- Spectometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

#### ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

DESCRIPTION

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		75	V
T <sub>stg</sub>	Storage Temperature	-20	+80	°C
To	Operating Temperature Range	-20	+60	°C
Ts	Soldering Temperature*		+220	°C
I <sub>L</sub>	Light Current		0.5	mA



400 500 600 700 800 900

WAVELENGTH (nm)

90 300 000

100 200

\*1/16 inch from case for 3 secs max

#### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current	H = 100 fc, 2850 K	0.9	1.2		m A
ΙD	Dark Current	$H = 0, V_R = 10 \text{ mV}$		200	333	pА
Rsн	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	30	50		MΩ
TC Rsh	RsH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{R} = 0 V^{**}$		10,000	12,000	pF
λrange	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	$\rm V_{_R}$ = 0 V, $\lambda$ = 254 nm	.12	.18		A/W
VBR	Breakdown Voltage	I = 10 μA	5	10		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 mV @ Peak		2.0x10 <sup>-14</sup>		W/ $\sqrt{Hz}$
tr	Response Time	$RL = 1 K\Omega V_R = 0 V$		2000		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.\*\*f = 1 MHz [FORM NO. 100-PDU-V110 REV N/C]

## with a quartz window.